

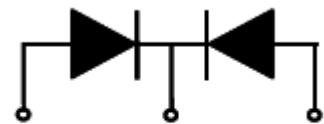


Product Specification

GOODARK Type

MBRF20150CT

Construction :: Schottky Barrier Rectifier
Application : For General Purpose
(Manufacturer) :
Suzhou Goodark Electronics Co.,Ltd
Prepared on Sep. 17th, 2008
Prepared: R & D Department
Approval: QRA Department



1. Anode 2.Cathode 3. Anode

**SCHOTTKY BARRIER
RECTIFIER
20 AMPERES
150 VOLTS**

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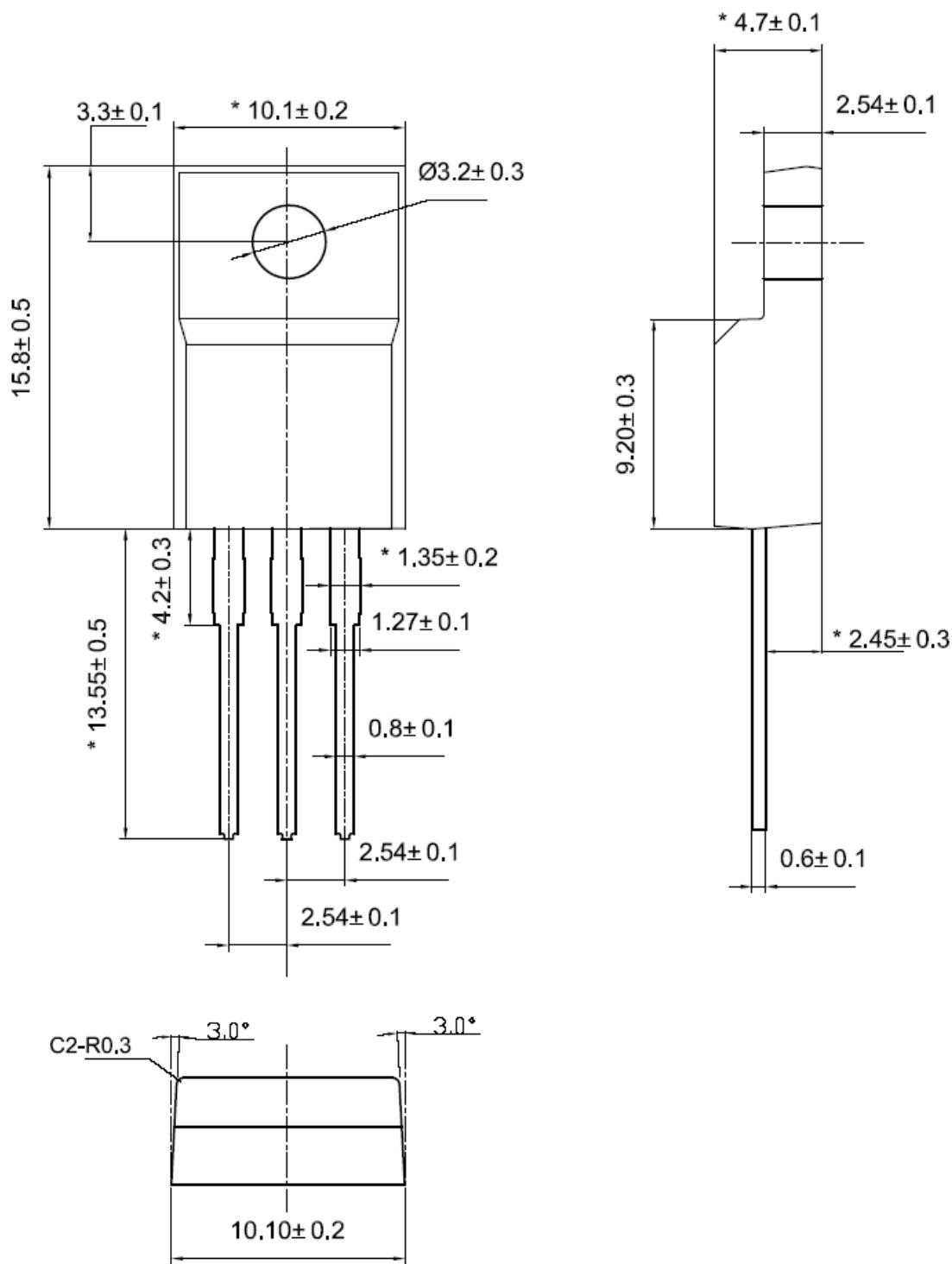
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1. Package Outline (TO220F)

UNIT:mm

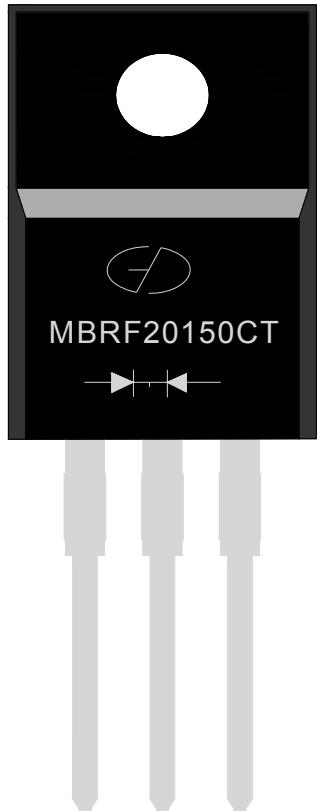


Lead Frame Material : Copper Plating: Pure Tin Plating





2. MARKING



1. Part Name : MBRF20150CT
2. Logo Mark:
3. Polarity:





3.Features& Mechanical Characteristics

Features

- Plastic package has underwriters Laboratory Flammability Classification 94V-0
- Dual rectifier construction, positive center tap
- Metal of silicon rectifier, majority carrier conduction
- Low forward voltage, high efficiency
- Guarding for over voltage protection
- For use in low voltage, high frequency inverters,
- Free wheeling, and polarity protection applications

Mechanical Characteristics

- Case: Epoxy, Molded
- Weight: 1.9grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max.for10 sec
- Shipped 50 units per plastic tube

4.Maximum Ratings and Electrical Characteristics

MAXIMUM RATINGS and ELECTRICAL CHARACTERISTICS(TC=25°C unless otherwise noted)				
PARAMETER	TEST CONDITIONS		MBRF20150CT	UNIT
Maximum repetitive peak reverse voltage		VRRM	150	V
Working peak reverse voltage		VRWM	150	V
Maximum DC blocking voltage		VDC	150	V
Maximum average forward rectified current at Tc=105°C total device per diode		IF(AV)	20 10	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load per diode		IFSM	150	A
Peak repetitive reverse current per leg at tp=2.0us , 1KHz		IRRM	1.0	A
Voltage rate of change (rated VR)		DV/dt	10000	V/us
Operating junction temperature range		TJ	-55 to +150	°C
Storage temperature range		TSTG	-55 to +150	°C
Isolation voltage (ITO-220AB only) from terminal to heatsink t = 1 sec		VAC	1500	V
Maximum instantaneous forward voltage per leg	IF=10A IF=10A	Tc=25°C Tc=125°C	0.92 0.75	V
Maximum reverse current per leg at working peak Reverse voltage		Tc=25°C Tc=100°C	0.2 6	mA

Thermal Characteristics Ta=25°C unless otherwise noted

Symbol	Parameter	Max	Unit
R _{θJC}	Thermal Resistance, Junction to Case per Leg	4.0	°C /W
R _{θJA}	Thermal Resistance, Junction to Ambient per Leg	62.5	°C /W

Note:

1. Screw mounting with 4-40 screw, where washer diameter is ≤4.9mm(0.19 ")
2. Pulse test:300us pulse width,1% duty cycle



5. Rating and Characteristic Curves

(TA = 25 °C unless otherwise noted)

Fig. 1: Average forward power dissipation versus average forward current (per diode).

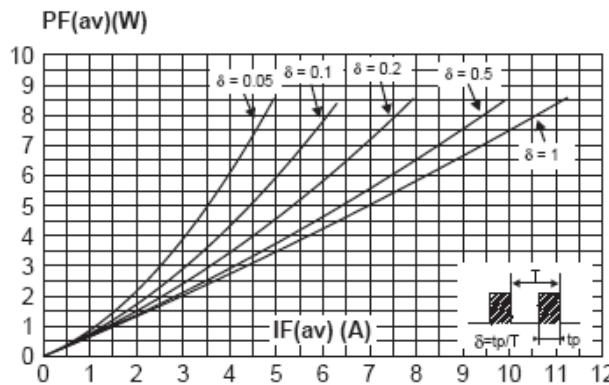


Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values, per diode).

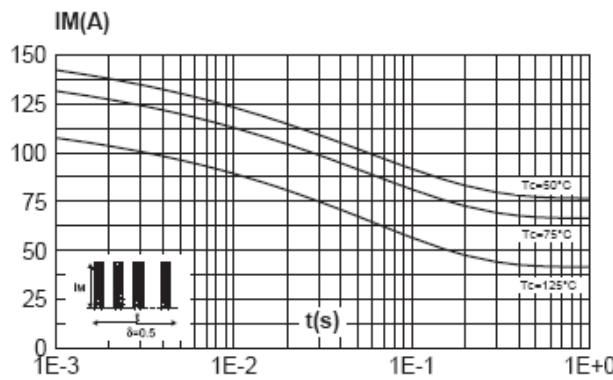


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values, per diode).

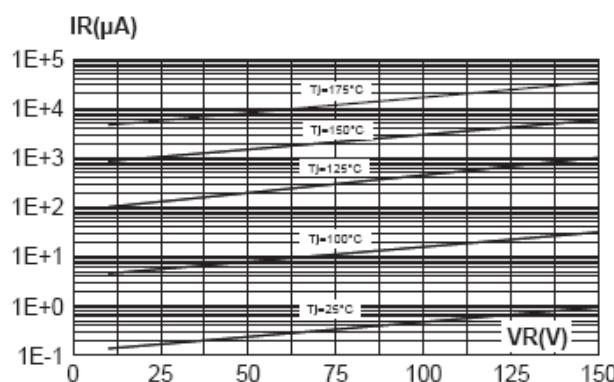


Fig. 2: Average forward current versus ambient temperature ($\delta = 0.5$, per diode).

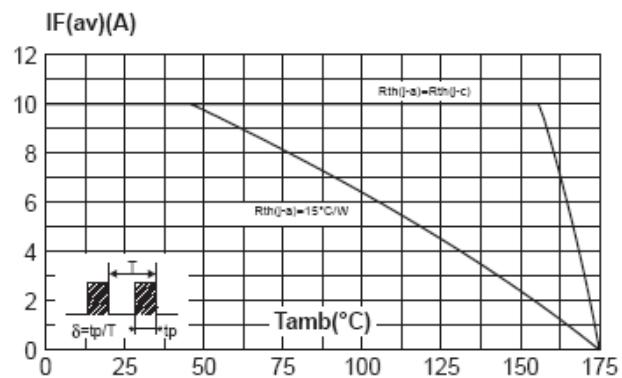


Fig. 4: Relative variation of thermal impedance junction to case versus pulse duration (per diode).

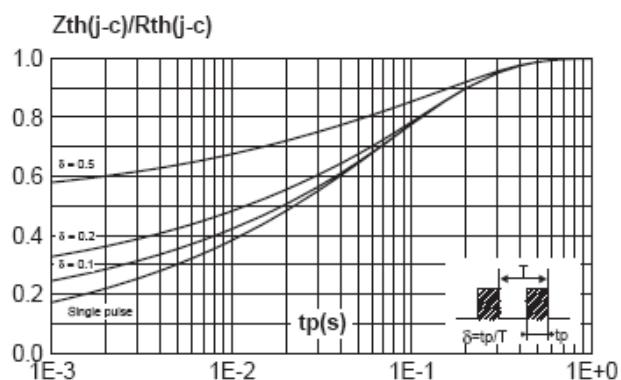
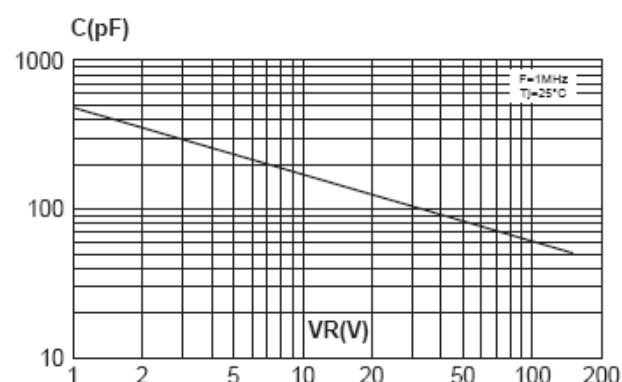


Fig. 6: Junction capacitance versus reverse voltage applied (typical values, per diode).





6. Packing Specification

1) Tube : 50units	2) Inner Box: 20 tube(1000units)
3) Outer Box: 10 inner box (10,000units)	

7. DESCRIPTION of BOX LABEL

	TYPE: Q'TY: P/O NO: LOT NO:
1) Inner Box Label	2) Inner Box Label
	TYPE: Q'TY: P/O NO:
3) Outer Box Label	4) Outer Box Label